NHPV08S600G, **NHPJ08S600G**

Switch Mode Power Rectifiers

Features

- Ultrafast 30 Nanosecond Recovery Time
- 150°C Operating Junction Temperature
- High Voltage Capability of 600 V
- Low Forward Drop
- Low Leakage Specified @ 125°C Case Temperature
- These Devices are Pb-Free and RoHS Compliant
- NHPJ08S600G is a Halogen Free/BFR Free Device

Mechanical Characteristics:

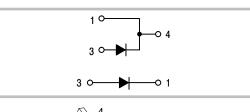
- Case: Epoxy, Molded
- Weight: 1.9 Grams (Approximately)
- Finish: All External Surfaces Corrosion Resistant and Terminal Leads are Readily Solderable
- Lead Temperature for Soldering Purposes: 260°C Max. for 10 Seconds

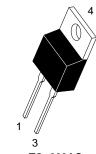


ON Semiconductor®

http://onsemi.com

PLANAR ULTRAFAST RECTIFIERS 8 A, 600 V



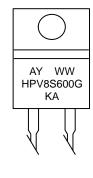




TO-220AC **CASE 221B**

TO-220 FULLPAK CASE 221AG

MARKING DIAGRAMS





= Assembly Location

= Year

ww

= Work Week G = Pb-Free Package

= Diode Polarity

ORDERING INFORMATION

See detailed ordering and shipping information in the package dimensions section on page 2 of this data sheet.

^{*}For additional information on our Pb-Free strategy and soldering details, please download the ON Semiconductor Soldering and Mounting Techniques Reference Manual, SOLDERRM/D.

NHPV08S600G, NHPJ08S600G

MAXIMUM RATINGS

Rating		Symbol	Value	Unit
Peak Repetitive Reverse Voltage Working Peak Reverse Voltage DC Blocking Voltage		V _{RRM} V _{RWM} V _R	600	V
Average Rectified Forward Current (Rated V _R)	TO-220AC TO-220FP	I _{F(AV)}	8 A @ T _C = 130°C 8 A @ T _C = 95°C	А
Peak Rectified Forward Current (Rated V _R , Square Wave, 20 kHz)	TO-220AC TO-220FP	I _{FRM}	8 A @ T _C = 125°C 8 A @ T _C = 85°C	А
Nonrepetitive Peak Surge Current (Surge applied at rated load conditions halfwave, single phase, 60 Hz)		I _{FSM}	80	Α
Operating Junction Temperature and Storage Temperature Range		T _J , T _{stg}	-55 to +150	°C

Stresses exceeding Maximum Ratings may damage the device. Maximum Ratings are stress ratings only. Functional operation above the Recommended Operating Conditions is not implied. Extended exposure to stresses above the Recommended Operating Conditions may affect device reliability.

THERMAL CHARACTERISTICS

Characteristic	Symbol	Value	Unit
NHPV08S600G: Thermal Resistance Junction-to-Case (Note 1)	$R_{ heta JC}$	1.5	°C/W
NHPJ08S600G: Thermal Resistance Junction–to–Case (Note 1)		4.25	°C/W

^{1.} Junction-to-Case shown as a typical value using a fixed 25°C cold plate boundary.

ELECTRICAL CHARACTERISTICS

Characteristic	Test Conditions	Symbol	Тур	Max	Unit
Instantaneous Forward Voltage (Note 2)	(i _F = 8 A, T _C = 125°C) (i _F = 8 A, T _C = 25°C)	VF	1.5 2.7	1.8 3.2	V
Instantaneous Reverse Current (Note 2)	(Rated DC Voltage, T _C = 125°C) (Rated DC Voltage, T _C = 25°C)	i _R	46 0.1	400 30	μΑ
Reverse Recovery Time	$(I_F = 0.5 \text{ A}, I_{rr} = 0.25 \text{ A}, I_R = 1 \text{ A})$ $(I_F = 1 \text{ A}, dI_F/dt = -50 \text{ A/}\mu\text{s}, V_R = 30 \text{ V})$	t _{rr}	- -	30 50	ns
Reverse Recovery Time Peak Reverse Recovery Current Total Reverse Recovery Charge Softness Factor	$(I_F = 8 \text{ A}, d_{IF}/d_t = -200 \text{ A/}\mu\text{s}, T_C = 25^{\circ}\text{C})$	t _{rr} I _{RM} Q _{rr} S	30 2.3 37 2	50 3 50 -	ns A nC -
Reverse Recovery Time Peak Reverse Recovery Current Total Reverse Recovery Charge Softness Factor	$(I_F = 8 \text{ A}, d_{IF}/d_t = -200 \text{ A/}\mu\text{s}, T_C = 125^{\circ}\text{C})$	t _{rr} I _{RM} Q _{rr} S	45 5.5 150 0.35	- - - -	ns A nC -
Forward Recovery Time Peak Forward Recovery Voltage	$(I_F = 8 \text{ A}, d_{IF}/d_t = 120 \text{ A/}\mu\text{s}, T_C = 25^{\circ}\text{C})$	t _{fr} V _{FP}	- -	200 6	ns V

^{2.} Pulse Test: Pulse Width = 300 μ s, Duty Cycle \leq 2.0%.

ORDERING INFORMATION

Device	Package	Shipping [†]
NHPV08S600G	TO-220AC (Pb-Free)	50 Units / Rail
NHPJ08S600G	TO-220FP (Pb-Free / Halide-Free)	50 Units / Rail

[†]For information on tape and reel specifications, including part orientation and tape sizes, please refer to our Tape and Reel Packaging Specifications Brochure, BRD8011/D.

NHPV08S600G, NHPJ08S600G

TYPICAL CHARACTERISTICS

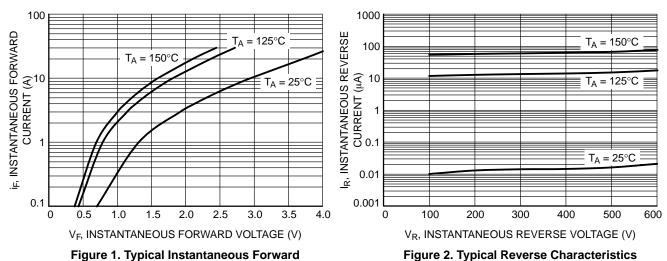


Figure 1. Typical Instantaneous Forward Characteristics

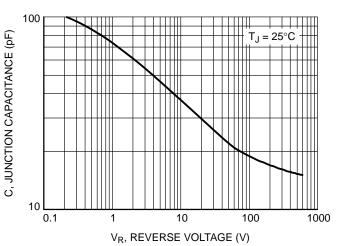


Figure 3. Typical Junction Capacitance

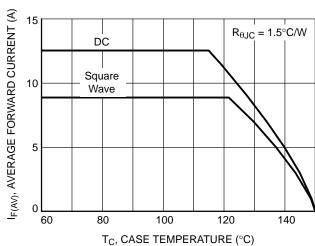


Figure 4. Current Derating TO-220AC

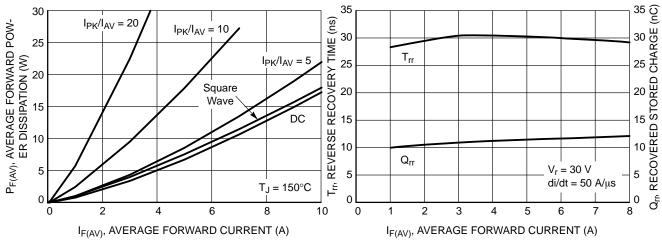


Figure 5. Forward Power Dissipation

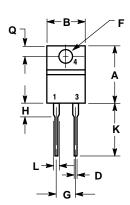
Figure 6. Typical Recovery Characteristics

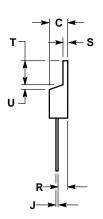
NHPV08S600G, NHPJ08S600G

PACKAGE DIMENSIONS

TO-220 TWO-LEAD

CASE 221B-04 ISSUE E



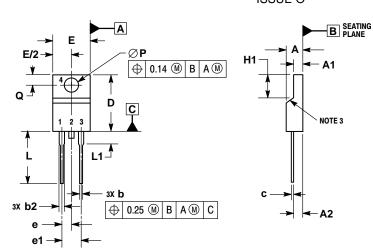


- DIMENSIONING AND TOLERANCING PER ANSI
- 2. CONTROLLING DIMENSION: INCH

	INCHES		MILLIN	IETERS
DIM	MIN	MAX	MIN	MAX
Α	0.595	0.620	15.11	15.75
В	0.380	0.405	9.65	10.29
С	0.160	0.190	4.06	4.82
D	0.025	0.035	0.64	0.89
F	0.142	0.161	3.61	4.09
G	0.190	0.210	4.83	5.33
Н	0.110	0.130	2.79	3.30
J	0.014	0.025	0.36	0.64
K	0.500	0.562	12.70	14.27
L	0.045	0.060	1.14	1.52
Q	0.100	0.120	2.54	3.04
R	0.080	0.110	2.04	2.79
S	0.045	0.055	1.14	1.39
T	0.235	0.255	5.97	6.48
U	0.000	0.050	0.000	1.27

TO-220 FULLPAK, 2-LEAD

CASE 221AG **ISSUE O**



- 1. DIMENSIONING AND TOLERANCING PER ASME Y14.5M, 1994. CONTROLLING DIMENSION: MILLIMETERS.

- CONTOUR UNCONTROLLED IN THIS AREA.
 DIMENSIONS D AND E DO NOT INCLUDE MOLD FLASH AND GATE PROTRUSIONS. MOLD FLASH AND GATE PROTRUSIONS NOT TO EXCEED 0.13 PER SIDE. THESE DIMENSIONS ARE TO BE MEASURED AT OUTERMOST EXTREME OF THE PLASTIC BODY
- 5. DIMENSION b2 DOES NOT INCLUDE DAMBAR PROTRUSION. LEAD WIDTH INCLUDING PROTRUSION

STIALL NOT EXCLED 2.00			
	MILLIMETERS		
DIM	MIN	MAX	
Α	4.30	4.70	
A1	2.50	2.90	
A2	2.50	2.70	
b	0.54	0.84	
b2	1.10	1.40	
С	0.49	0.79	
D	14.22	15.88	
E	9.65	10.67	
е	2.54 BSC		
e1	5.08 BSC		
H1	5.97	6.48	
L	12.70	14.73	
L1	-	2.80	
P	3.00	3.40	
Q	2.80	3.20	

ON Semiconductor and iii) are registered trademarks of Semiconductor Components Industries, LLC (SCILLC). SCILLC owns the rights to a number of patents, trademarks, copyrights, trade secrets, and other intellectual property. A listing of SCILLC's product/patent coverage may be accessed at www.onsemi.com/site/pdf/Patent-Marking.pdf. SCILLC reserves the right to make changes without further notice to any products herein. SCILLC makes no warranty, representation or guarantee regarding the suitability of its products for any particular purpose, nor does SCILLC assume any liability arising out of the application or use of any product or circuit, and specifically disclaims any and all liability, including without limitation special, consequential or incidental damages. "Typical" parameters which may be provided in SCILLC data sheets and/or specifications can and do vary in different applications and actual performance may vary over time. All operating parameters, including "Typicals" must be validated for each customer application by customer's technical experts. SCILLC does not convey any license under its patent rights nor the rights of others. SCILLC products are not designed, intended, or authorized for use as components in systems intended for surgical implant into the body, or other applications intended to support or sustain life, or for any other application in which the failure of the SCILLC product could create a situation where personal injury or death may occur. Should Buyer purchase or use SCILLC products for any such unintended or unauthorized application, Buyer shall indemnify and hold SCILLC and its officers, employees, subsidiaries, affiliates, and distributors harmless against all claims, costs, damages, and expenses, and reasonable attorney fees arising out of, directly, any claim of personal injury or death associated with such unintended or unauthorized use, even if such claim alleges that SCILLC was negligent regarding the design or manufacture of the part. SCILLC is an Equal Opportunity/Affirmative Action Employer. This literature is subject to all applicable copyright laws and is not for resale in any manner.

PUBLICATION ORDERING INFORMATION

LITERATURE FULFILLMENT

Literature Distribution Center for ON Semiconductor P.O. Box 5163, Denver, Colorado 80217 USA

Phone: 303-675-2175 or 800-344-3860 Toll Free USA/Canada Fax: 303-675-2176 or 800-344-3867 Toll Free USA/Canada Email: orderlit@onsemi.com

N. American Technical Support: 800-282-9855 Toll Free

Europe, Middle East and Africa Technical Support: Phone: 421 33 790 2910

Japan Customer Focus Center Phone: 81-3-5817-1050

ON Semiconductor Website: www.onsemi.com

Order Literature: http://www.onsemi.com/orderlit

For additional information, please contact your local Sales Representative